

IN THE CLAIMS

Claims 1 - 16 (Cancelled)

17. (Currently Amended) An integrated circuit (IC) comprising:
a substrate comprising at least one level of interconnection;
an oxide insulating layer formed directly on a surface of the substrate;
at least one conductive structure formed directly on the insulating layer, the conductive structure comprising a contact to the at least one level of interconnection of the substrate;
an adhesion layer formed on a top surface of said oxide insulating layer ~~by treating said surface of said oxide layer with a gas~~; and
a first passivation layer formed on a top surface of said adhesion layer and a top surface of the conductive structure, said first passivation layer and said adhesion layer including at least one common chemical element.
18. (Original) The integrated circuit of claim 17 further comprising a second passivation layer formed upon said first passivation layer.
19. (Currently Amended) The integrated circuit of claim 17 wherein said oxide insulating layer includes comprises an oxide layer comprising silicon dioxide (SiO_2).
20. (Original) The integrated circuit of claim 17 wherein said adhesion layer includes silicon oxynitride.
21. (Original) The integrated circuit of claim 17 wherein said first passivation layer includes silicon nitride (Si_3N_4).
22. (Original) The integrated circuit of claim 18 wherein said second passivation layer includes polyimide.
23. (Currently Amended) An integrated circuit comprising in a ~~three~~four layer stack:
a silicon dioxide insulating layer;
a silicon oxynitride adhesion layer formed on a surface of said silicon dioxide insulating layer by treating said surface of said silicon dioxide insulating layer with a gas; ~~and~~
a silicon nitride hard passivation layer formed directly on a surface of said silicon oxynitride adhesion layer; ~~and~~
a photodefinable polyimide soft passivation layer formed on said silicon nitride hard passivation layer.

24. (Cancelled)

25. (Previously Presented) The integrated circuit of claim 17, wherein said gas includes one of oxygen and nitrogen (N), oxygen and ammonia (NH₃), oxygen and argon (Ar) and ozone (O₃) and argon.

26. (Previously Presented) The integrated circuit of claim 23, wherein said gas includes one of oxygen and nitrogen (N), oxygen and ammonia (NH₃), oxygen and argon (Ar) and ozone (O₃) and argon.

27. (Currently Amended) An integrated circuit comprising:

a substrate;

an insulating layer formed on the substrate;

at least one conductive structure formed directly on the insulating layer;

~~a composite film formed on the substrate, the composite film comprising:~~

~~a first layer comprising silicon dioxide,~~

~~a second-first layer formed from a modification of a portion of the first-insulating layer, and a third-second layer of a material different than a material of the second-first layer,~~

~~wherein the second-first layer is disposed between the first-insulating layer and the third-second layer, and~~

~~wherein the second-first layer and the third-second layer comprise one common chemical element other than silicon; and~~

~~wherein the third-second layer is a passivation layer formed on the second-first layer.~~

28. (Currently Amended) The integrated circuit of claim 27 wherein said second-first layer includes silicon oxynitride.

29. (Currently Amended) The integrated circuit of claim 27 wherein said third-second layer includes silicon nitride (Si₃N₄).